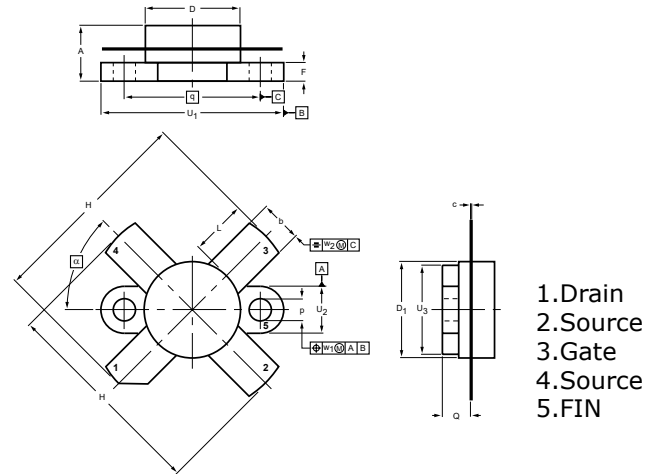


DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS transistor is designed for broadband HF and VHF applications.

FEATURES

- Output Power: 150 W
- Power Gain: 15 dB Typ@30M, 28V
- Efficiency: 40% Typ@30M, 28V



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V _{DSS}	65	V
Drain-Gate Voltage	V _{DGR}	65	V
Gate-Source Voltage	V _{GS}	±40	V
Drain Current — Continuous	I _D	16	A
Total Device Dissipation	P _D	300	W
Junction Temperature	T _J	200	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =100mA, V _{GS} =0	65	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =28V	-	-	5	mAdc
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V	-	-	1	uAdc
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 10 V, I _D = 100mA	1.0	3.0	5.0	V
Forward Transconductance	g _{fs}	V _{DS} = 10 V, I _D = 5A	4	7	-	mhos
Input Capacitance	C _{iss}	V _{DS} = 28 V, V _{GS} = 0 V, f = 1.0 MHz	-	460	-	pF
Output Capacitance	C _{oss}		-	320	-	pF
Reverse Transfer Capacitance	C _{rss}		-	30	-	pF
Common Source Power Gain	G _{PS}	V _{DD} =28V, P _{OUT} =150W, f=30MHz, I _{DQ} = 250 mA	-	15.0	-	dB
Drain Efficiency	η _D	V _{DD} =28V, P _{OUT} =150W, f=150MHz, I _{DQ} = 250mA	-	40.0	-	%
Common Source Power Gain	G _{PS}	V _{DD} =28V, P _{OUT} =150W, f=150MHz, I _{DQ} = 250mA	-	6.0	-	dB
Intermodulation Distortion	IMD3	V _{DD} = 28 V, P _{out} = 150 W (PEP), f ₁ = 30 MHz, f ₂ = 30.001 MHz, I _{DQ} = 250 mA	-	-30	-	dB

Note : Above parameters , ratings , limits and conditions are subject to change.